Bo Song

List of Publications by Citations

29 papers	1,349 citations	15 h-index	34 g-index
34 ext. papers	1,555 ext. citations	3.7 avg, IF	3.75 L-index

#	Paper	IF	Citations
29	InAlN/AlN/GaN HEMTs With Regrown Ohmic Contacts and f_{T} of 370 GHz. *IEEE Electron Device Letters*, **2012**, 33, 988-990	4.4	252
28	Esaki Diodes in van der Waals Heterojunctions with Broken-Gap Energy Band Alignment. *Nano Letters*, **2015**, 15, 5791-8	11.5	237
27	. *IEEE Electron Device Letters*, **2015**, 36, 375-377	4.4	126
26	1.7-kV and 0.55- $text{m}Omega cdot text {cm}^{2}$ GaN p-n Diodes on Bulk GaN Substrates With Avalanche Capability. *IEEE Electron Device Letters*, **2016**, 37, 161-164	4.4	125
25	Near unity ideality factor and Shockley-Read-Hall lifetime in GaN-on-GaN p-n diodes with avalanche breakdown. *Applied Physics Letters*, **2015**, 107, 243501	3.4	117
24	Gate-recessed integrated E/D GaN HEMT technology with fT/fmax >300 GHz. *IEEE Electron Device Letters*, **2013**, 34, 741-743	4.4	70
23	Ultrascaled InAlN/GaN High Electron Mobility Transistors with Cutoff Frequency of 400 GHz. *Japanese Journal of Applied Physics*, **2013**, 52, 08JN14	1.4	55
22	Polarization-Induced GaN-on-Insulator E/D Mode p-Channel Heterostructure FETs. *IEEE Electron Device Letters*, **2013**, 34, 852-854	4.4	49
21	High breakdown single-crystal GaN p-n diodes by molecular beam epitaxy. *Applied Physics Letters*, **2015**, 107, 232101	3.4	44
20	Quaternary Barrier InAlGaN HEMTs With f_{T}/f_{max} of 230/300 GHz. *IEEE Electron Device Letters*, **2013**, 34, 378-380	4.4	42
19	Two-dimensional electron gases in strained quantum wells for AlN/GaN/AlN double heterostructure field-effect transistors on AlN. *Applied Physics Letters*, **2014**, 104, 193506	3.4	35
18	High Holding Voltage SCR-LDMOS Stacking Structure With Ring-Resistance-Triggered Technique. *IEEE Electron Device Letters*, **2013**, 34, 1178-1180	4.4	35
17	Strained GaN quantum-well FETs on single crystal bulk AlN substrates. *Applied Physics Letters*, **2017**, 110, 063501	3.4	34
16	Ultralow-Leakage AlGaN/GaN High Electron Mobility Transistors on Si With Non-Alloyed Regrown Ohmic Contacts. *IEEE Electron Device Letters*, **2016**, 37, 16-19	4.4	26
15	. *IEEE Transactions on Electron Devices*, **2014**, 61, 747-754	2.9	23
14	Impact of CF4plasma treatment on threshold voltage and mobility in Al2O3/InAlN/GaN MOSHEMTs. *Applied Physics Express*, **2014**, 7, 031002	2.4	15
13	Steep Sub-Boltzmann Switching in AlGaN/GaN Phase-FETs With ALD VO2. *IEEE Transactions on Electron Devices*, **2018**, 65, 945-949	2.9	11

List of Publications

12	Dual optical marker Raman characterization of strained GaN-channels on AlN using AlN/GaN/AlN quantum wells and 15N isotopes. *Applied Physics Letters*, **2015**, 106, 041906	3.4	10
11	Electron mobility in polarization-doped Al0-0.2GaN with a low concentration near 1017 cm□. *Applied Physics Letters*, **2017**, 110, 182102	3.4	8
10	AlGaN/GaN HEMTs on Si by MBE with regrown contacts and fT = 153 GHz. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2014**, 11, 887-889		8
9	Unique opportunity to harness polarization in GaN to override the conventional power electronics figure-of-merits **2015**,		5
8	Monolithically integrated E/D-mode InAlN HEMTs with □/□max > 200/220 GHz **2012**,		5
7	Compact MOS-triggered SCR with faster turn-on speed for ESD protection. *Microelectronics Reliability*, **2010**, 50, 1393-1397	1.2	5
6	A Novel Capacitance-Coupling-Triggered SCR for Low-Voltage ESD Protection Applications. *IEEE Electron Device Letters*, **2010**, 31, 1089-1091	4.4	4
5	High-voltage polarization-induced vertical heterostructure p-n junction diodes on bulk GaN substrates **2015**,		3
4	GaN lateral PolarSJs: Polarization-doped super junctions **2014**,		2
3	Trigger voltage walk-in effect of ESD protection device in HVCMOS **2010**,		2
2	Comparing buffer leakage in PolarMOSH on SiC and free-standing GaN substrates **2016**,		1
1	Distributed polarization-doped GaN p□ diodes with near-unity ideality factor and avalanche breakdown voltage of 1.25 kV. *Applied Physics Letters*, **2022**, 120, 122111	3.4	0